

REMARKS/ARGUMENTS

Claims 11, 14, and 19-22 stand rejected under 35 U.S.C. 102(b) as being anticipated by Hsu; claims 12 and 13 stand rejected under 35 U.S.C. 103(a) as being unpatentable over Hsu in view of Lin.

In forming the rejection of the claims in the instant invention the examiner states that the patterned gate structure formed over the first active region, the second active region and the contact region, and contact regions of the same conductivity type as the well are not recited in the rejected claims.

Referring to Figures 2(a) and 2(b) of the instant disclosure, the examiner is directed to claim 11 which comprises the limitations of forming at least a first 60 and second 65 active regions in said well region 20 by forming a contact isolation structure 32 in said well region between said first isolation region and said second isolation region, forming a gate dielectric layer 40 on said first active region and said second active region, and forming a gate layer 50 on said gate dielectric layer wherein said gate layer overlies said first active region 60, said second active region 65, and said contact isolation region 32. All the limitations to which the examiner refers in the response dated 12/10/2004 are clearly described in claim 11.

The examiner is now directed to the Hsu patent where, in Figure 2, first and second active regions are formed by forming the isolation structure 34. The subsequent gate structure 46 in the Hsu patent extends only over one of the active regions formed in Figure 2. From Figure 7 of the Hsu patent, this would be the active region formed to the left of the isolation structure 34. Claim 11 requires the gate layer (46 in the Hsu patent) to overlie said first active region, said second active region, and said contact isolation region. This is not shown in the Hsu patent and claim 11 is allowable over the Hsu patent under 102(b). Furthermore, claims 12-14 depend on claim 11 and therefore contain all the limitations of claim 11. The Lin patent does not

contain the feature described above and claims 12-14 are therefore also allowable over the Hsu patent either singly or in combination with the Lin patent.

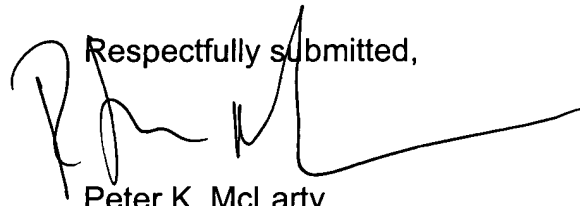
Claim 19 comprises the limitations of forming a well region of a first conductivity type in a semiconductor substrate; forming a gate dielectric layer on said well region; forming a gate layer on said gate dielectric layer; forming contact regions in said well region of a first conductivity type wherein said contact regions are formed using a source and drain region implantation formation process; and forming gate layer contacts to said gate conductive layer wherein said gate layer contacts overlie an isolation region. The examiner is directed, in Fig 2(a) of the instant invention, to the limitations of the contacts to the well region 35 being of the same conductivity type as the well region 20. This limitation is clearly contained in claim 11. The Hsu patent teaches in col. 4, lines 41-46 that the source and drain regions 60, 62 are of opposite conductivity type to the well region 63. The well region 63 is p-type and the source and drain regions 60, 62 are n-type. Claim 19 is therefore allowable over the Hsu patent. Furthermore, claims 20-22 depend on claim 19 and therefore contain all the limitations of claim 11. Claims 20-22 are therefore also allowable over the cited art.

In light of the above, it is respectfully submitted that the present application is in condition for allowance, and notice to that effect is respectfully requested.

While it is believed that the instant amendment places the application in condition for allowance, should the Examiner have any further comments or suggestions, it is respectfully requested that the Examiner contact the undersigned in order to expeditiously resolve any outstanding issues.

To the extent necessary, Applicants petition for an Extension of Time under 37 CFR 1.136. Please charge any fees in connection with the filing of this paper, including

extension of time fees, to the deposit account of Texas Instruments Incorporated,
Account No. 20-0668.

Respectfully submitted,

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Amendments to the Drawings:

None